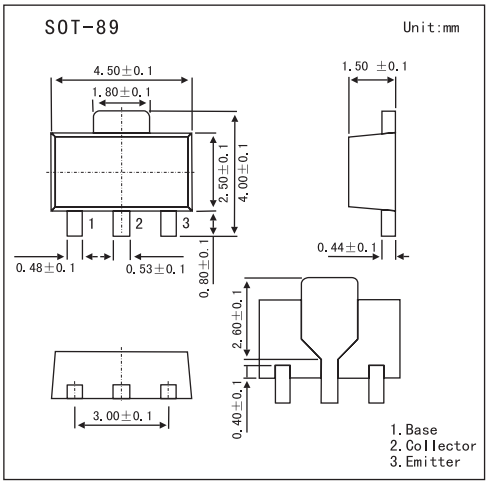
PNP Epitaxial Silicon Transistor

KSA1201



■ Features

- Collector-Emitter Voltage: V_{CEO}= -120V
- f_T=120MHz
- Collector Power Dissipation P_C=1 to 2W : Mounted on Ceramic Board

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-120	V
Collector-Emitter Voltage	V_{CEO}	-120	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-800	mA
Base Current	I_B	-160	mA
Collector Power Dissipation	P_C	500	mW
	P_C*	1,000	mW
Junction Temperature	T_J	150	℃
Storage Temperature	T_{STG}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C= -10mA, I_B=0	120			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E= -1mA, I_C=0	-5			V
Collector Cut-off Current	I_{CBO}	V_{CB}= -120V, I_E=0			-100	nA
Emitter Cut-off Current	I_{EBO}	V_{BE}= -5V, I_C=0			-100	nA
DC Current Gain	h_{FE}	V_{CE}= -5V, I_C= -100mA	80		240	
Collector-Emitter Saturation Voltage	$V_{CE\ (sat)}$	I_C= -500mA, I_B=-50mA			-1.0	V
Base-Emitter On Voltage	$V_{BE\ (on)}$	V_{CE}= -5V, I_C= -500mA			-1.0	V
Current Gain Bandwidth Product	f_T	V_{CE}= -5V, I_C= -100mA		120		MHz
Output Capacitance	C_{ob}	V_{CB}= -10V, I_E=0, f=1MHz			30	pF

■ h_{FE} Classification

Marking	SDO	SDY
Rank	O	Y
Type	80～160	120～240